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FDP054N10 N-Channel PowerTrench[®] MOSFET 100 V, 144 A, 5.5 m Ω

Features

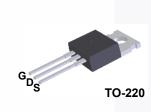
- $R_{DS(on)}$ = 4.6 m Ω (Typ.) @ V_{GS} = 10 V, I_D = 75 A
- · Fast Switching Speed
- Low Gate Charge
- High Performance Trench Technology for Extremely Low $R_{\text{DS}(\text{on})}$
- High Power and Current Handling Capability
- RoHS Compliant

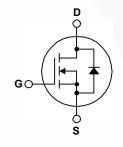
Description

This N-Channel MOSFET is produced using Fairchild Semiconductor's advanced PowerTrench[®] process that has been tailored to minimize the on-state resistance while maintaining superior switching performance.

Applications

- Synchronous Rectification for ATX / Server / Telecom PSU
- Battery Protection Circuit
- Motor Drives and Uninterruptible Power Supplies
- Micro Solar Inverter





MOSFET Maximum Ratings T_C = 25°C unless otherwise noted.

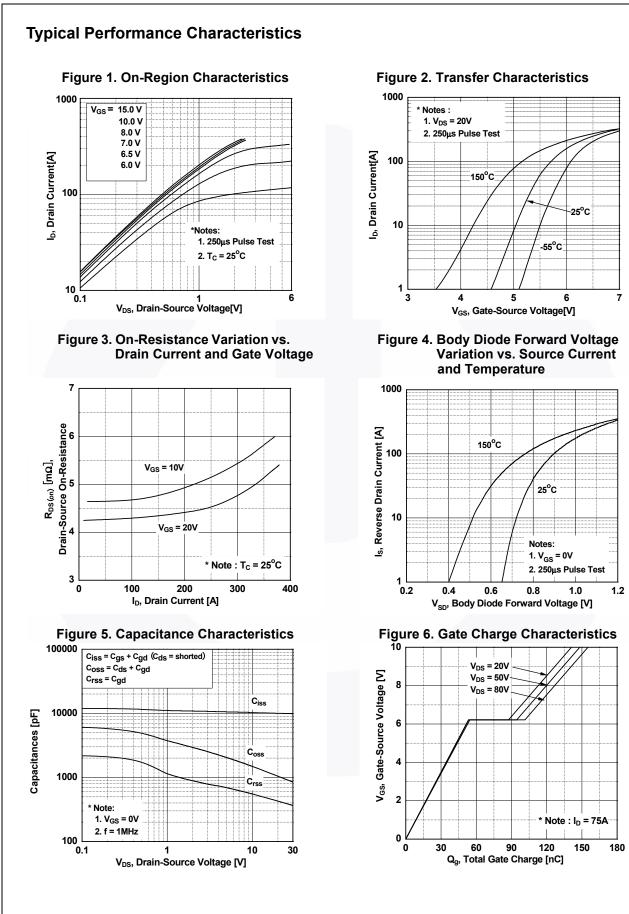
Symbol		Parameter			
V _{DSS}	Drain to Source Voltage	100	V		
V _{GSS}	Gate to Source Voltage		±20	V	
ID		- Continuous (T _C = 25 ^o C, Silicon Limited)	144	A	
	Drain Current	- Continuous (T _C = 100 ^o C, Silicon Limited)	102		
		- Continuous (T _C = 25 ^o C, Package Limited)	120		
I _{DM}	Drain Current	- Pulsed (Note 1)	576	А	
E _{AS}	Single Pulsed Avalanche Energy (Note 2)		1153	mJ	
dv/dt	Peak Diode Avalanche Energy (Note 3)		6	V/ns	
P _D	Dower Dissinction	(T _C = 25°C)	263	W	
	Power Dissipation	- Derate Above 25°C	1.75	W/ºC	
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +175	°C	
ΤL	Maximum Lead Temperatu	re for Soldering, 1/8" from Case for 5 Seconds	300	°C	

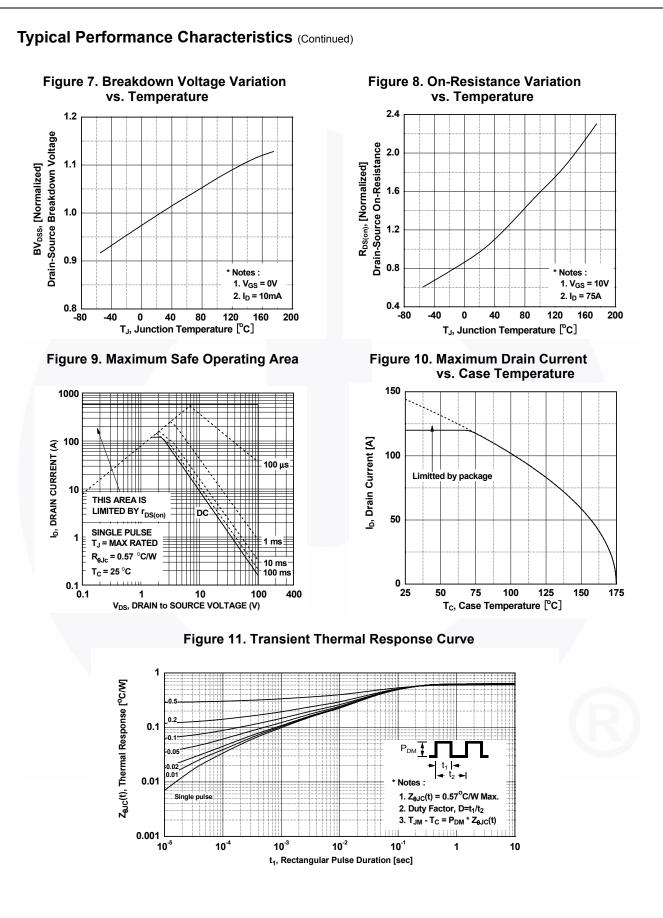
Thermal Characteristics

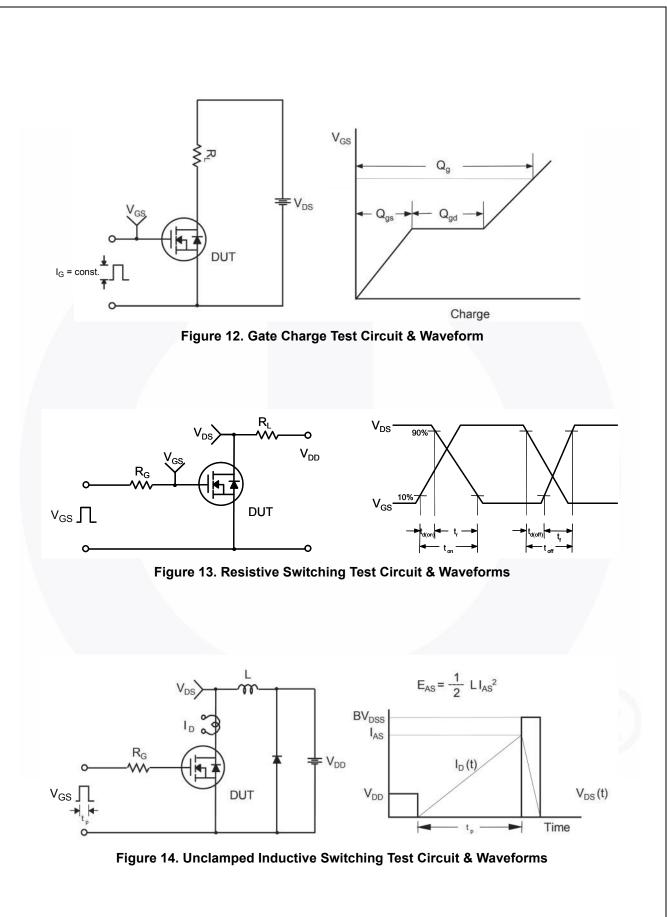
Symbol	Parameter	FDP054N10	Unit
$R_{ extsf{ heta}JC}$	Thermal Resistance, Junction to Case, Max.	0.57	°C/W
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient, Max.	62.5	°C/W

November 2013

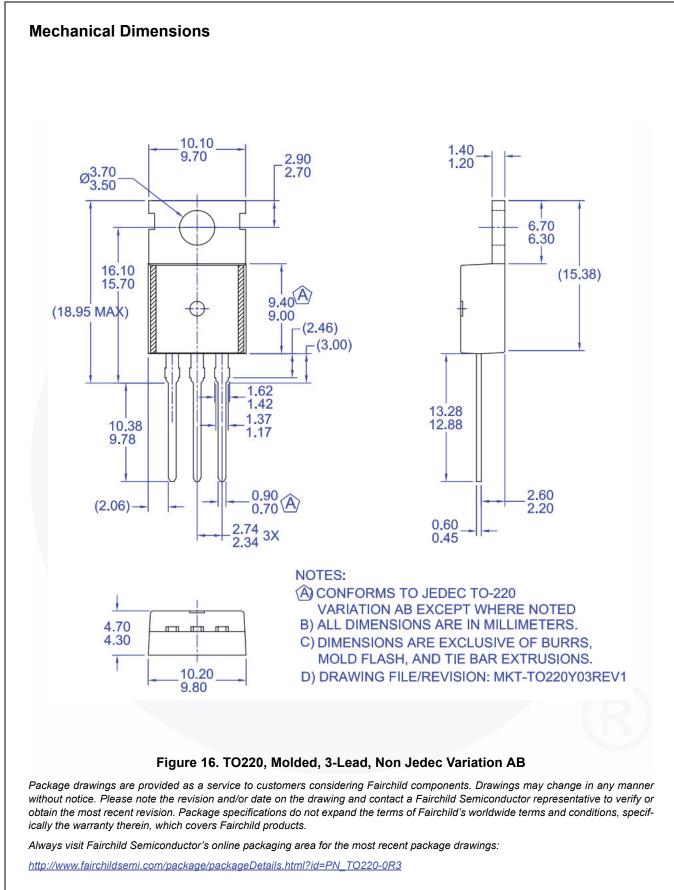
IN10	FDP054N10	Package TO-220	Packing Method Tube	N/A		N/A		
al Chara	Icteristics T _c = 25°C						Quantity 50 units	
		unless ot	herwise noted.		1			
	Parameter		Test Condit	tions	Min.	Тур.	Max.	Unit
cteristics								
			$p = 250 \mu\text{A}, V_{GS} = 0^{-1}$	V, T _C = 25°C	100	-	-	V
Breakdown Voltage Temperature Coefficient			$I_D = 250 \ \mu$ A, Referenced to 25° C		-	0.01	-	V/ºC
Zero Cat	Zoro Cato Valtago Droin Current		/ _{DS} = 100 V, V _{GS} = 0	V	-	-	1	
Zero Gale vollage Drain Current			V_{DS} = 100 V, V_{GS} = 0 V, T_{C} = 150°C		-	-	500	μA
Gate to E	Body Leakage Current	١	$V_{\rm GS} = \pm 20 \text{ V}, \text{ V}_{\rm DS} = 0$	V	-	-	±100	nA
cteristics								
-		N	V _{GS} = V _{DS} , I _D = 250 ι	ιA	2.5	3.5	4.5	V
					-	4.6	5.5	mΩ
Forward	Transconductance				-	192	-	S
Character	riation					1		
						0095	12280	~
		· · ·	$V_{DS} = 25 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	V,	-			pF
	-		f = 1 MHz		-			pF
		,	/ 00.)/ 1 75.4		-			pF nC
				,	-		203	nC
	°						-	nC
						10		
							1	
		, ·	$V_{DD} = 50 \text{ V}, \text{ I}_{D} = 75 \text{ A},$ $V_{CS} = 10 \text{ V}, \text{ R}_{C} = 4.7 \Omega$		-			ns
					-		-	ns
	,			_	-		-	ns
Turn-Off	Fall Time			(Note 4)	-	39	88	ns
rce Diod	e Characteristics							
Maximum	Continuous Drain to Sourc	e Diode I	Forward Current		7 -	-	144	Α
Maximum	Pulsed Drain to Source Di	ode Forw	orward Current		-	-	576	Α
Drain to S	Source Diode Forward Volta	ıge ۱	V _{GS} = 0 V, I _{SD} = 75 A		-	-	1.3	V
Reverse I	Recovery Time				-	57	-	ns
Reverse I	Recovery Charge	C	dI _F /dt = 100 Ā/μs		-	121	-	nC
	Drain to S Breakdow Coefficient Zero Gat Gate to E Cteristics Gate Thr Static Dra Forward Character Total Gat Gate to S Gate to S Gate to D Character Total Gat Gate to S Gate to D Character Turn-On I Turn-On I Turn-Off I Turn-Off I Turn-Off I Turn-Off I Turn-Off I Turn-Off I Turn-Off I Turn-Off I	Drain to Source Breakdown Voltage Breakdown Voltage Temperature Coefficient Zero Gate Voltage Drain Current Gate to Body Leakage Current Cteristics Gate Threshold Voltage Static Drain to Source On Resistance Forward Transconductance Characteristics Input Capacitance Output Capacitance Reverse Transfer Capacitance Total Gate Charge at 10V Gate to Source Gate Charge Gate to Drain "Miller" Charge Characteristics Turn-On Delay Time Turn-On Rise Time Turn-Off Delay Time Turn-Off Fall Time Ince Diode Characteristics Maximum Continuous Drain to Source Di	Drain to Source Breakdown Voltage I Breakdown Voltage Temperature Coefficient I Zero Gate Voltage Drain Current N Gate to Body Leakage Current N cteristics Gate Threshold Voltage Static Drain to Source On Resistance N Forward Transconductance N Characteristics Input Capacitance Output Capacitance N Quiput Capacitance N Gate to Drain "Miller" Charge N Gate to Drain "Miller" Charge N Characteristics Turn-On Delay Time Turn-On Rise Time N Turn-Off Delay Time N Turn-Off Fall Time N Maximum Continuous Drain to Source Diode Forw Drain to Source Diode Forward Voltage Reverse Recovery Time N	Drain to Source Breakdown Voltage $I_D = 250 \ \mu$ A, $V_{GS} = 0^{-1}$ Breakdown Voltage Temperature Coefficient $I_D = 250 \ \mu$ A, ReferenceZero Gate Voltage Drain Current $V_{DS} = 100 \ V, \ V_{GS} = 0$ Gate to Body Leakage Current $V_{GS} = 100 \ V, \ V_{GS} = 0$ Gate Threshold Voltage $V_{GS} = 250 \ \mu$ A, $V_{GS} = 0$ Static Drain to Source On Resistance $V_{GS} = 10 \ V, \ I_D = 75 \ A$ Forward Transconductance $V_{GS} = 10 \ V, \ I_D = 75 \ A$ CharacteristicsInput CapacitanceInput Capacitance $V_{GS} = 10 \ V, \ I_D = 75 \ A$ Gate to Source Gate Charge $V_{GS} = 10 \ V$ Total Gate Charge at 10V $V_{DS} = 80 \ V, \ I_D = 75 \ A$ Gate to Drain "Miller" Charge $V_{GS} = 10 \ V, \ G_S = 10$	Drain to Source Breakdown VoltageID = 250 μA, VGS = 0 V, TC = 25°CBreakdown Voltage Temperature CoefficientID = 250 μA, Referenced to 25°CJe = 250 μA, Referenced to 25°CID = 250 μA, Referenced to 25°CZero Gate Voltage Drain Current $V_{DS} = 100 V, V_{GS} = 0 V$ Gate to Body Leakage Current $V_{GS} = 100 V, V_{GS} = 0 V$ CteristicsStatic Drain to Source On Resistance $V_{GS} = \pm 20 V, V_{DS} = 0 V$ Gate Threshold Voltage $V_{GS} = V_{DS}, I_D = 250 μA$ Static Drain to Source On Resistance $V_{GS} = 10 V, I_D = 75 A$ Forward Transconductance $V_{GS} = 10 V, I_D = 75 A$ CharacteristicsInput CapacitanceInput Capacitance $V_{DS} = 25 V, V_{GS} = 0 V, f = 1 MHz$ Reverse Transfer Capacitance $V_{DS} = 80 V, I_D = 75 A, V_{GS} = 10 V$ Gate to Drain "Miller" ChargeV_DS = 80 V, I_D = 75 A, V_{GS} = 10 V, I_S	$\begin{tabular}{ c c c c c } \hline Drain to Source Breakdown Voltage II_D = 250 \ \mu A, \ V_{GS} = 0 \ V, \ T_C = 25^\circ C & 100 \\ \hline Breakdown Voltage Temperature Coefficient & I_D = 250 \ \mu A, \ Referenced to 25^\circ C & - \\ \hline I_D = 250 \ \mu A, \ Referenced to 25^\circ C & - \\ \hline V_{DS} = 100 \ V, \ V_{GS} = 0 \ V, \ T_C = 150^\circ C & - \\ \hline V_{DS} = 100 \ V, \ V_{GS} = 0 \ V, \ T_C = 150^\circ C & - \\ \hline Ceristics & & & & & & & & & & & & & & & & & & &$	$\begin{tabular}{ c $	$\begin{tabular}{ c c c c c c } \hline V_{DS} = 0 V, T_C = 25^{\circ}C$ 100 \\ \hline P_{D} = 250 μA, R_{GS} = 0 V, T_C = 25^{\circ}C$ - 0.01 - \\ \hline V_D = 100 V, V_{GS} = 0 V 1 \\ \hline V_D = 100 V, V_{GS} = 0 V, T_C = 150^{\circ}C$ 500 \\ \hline Q_D = 100 V, V_{GS} = 0 V, T_C = 150^{\circ}C$ 1 \\ \hline V_{DS} = 100 V, V_{GS} = 0 V, T_C = 150^{\circ}C$ 1 \\ \hline V_{DS} = 100 V, V_{GS} = 0 V, T_C = 150^{\circ}C$ 1 \\ \hline V_{DS} = 100 V, V_{GS} = 0 V, T_C = 150^{\circ}C$ 1 \\ \hline V_{DS} = 100 V, V_{GS} = 0 V, T_C = 150^{\circ}C$ 1 \\ \hline V_{DS} = 100 V, V_{GS} = 0 V, T_C = 150^{\circ}C$ 1 \\ \hline V_{DS} = 100 V, V_{DS} = 0 V 1 \\ \hline V_{DS} = 100 V, V_{DS} = 0 V 1 \\ \hline V_{DS} = 100 V, V_{DS} = 10 V, V_D = 75 A - 192 - \\ \hline V_{CA} = 10 V_{CS}$ = 10 V, V_D = 75 A - 192 - \\ \hline V_{DS} = 25 V, V_{GS} = 0 V, $10 = 75 A - 192 - \\ \hline V_{DS} = 25 V, V_{GS} = 0 V, $10 = 75 A - 192 - \\ \hline V_{DS} = 25 V, V_{GS} = 0 V, $10 = 75 A - 192 - \\ \hline V_{DS} = 25 V, V_{GS} = 0 V, $10 = 75 A - 192 - \\ \hline V_{DS} = 25 V, V_{GS} = 0 V, $10 = 75 A - 192 - \\ \hline V_{DS} = 25 V, V_{GS} = 0 V, $10 = 75 A - 192 - \\ \hline V_{DS} = 10 V & V_{DS} = 80 V, $10 = 75 A, $166 - 203 - 128 - \\ \hline V_{DS} = 10 V & V_{DS} = 80 V, $10 = 75 A, $166 - 203 - \\ \hline Q_{S} = 10 V & V_{DS} = 10 V $







DUT + V_{DS} a ۱_{sd} م L Driver R_G€ Same Type as DUT L F ∨_{DD} $\prod V_{GS}$ • dv/dt controlled by R_{G} • I_{SD} controlled by pulse period Î Gate Pulse Width V_{GS} D = Gate Pulse Period 10V (Driver) I_{FM}, Body Diode Forward Current I _{SD} di/dt (DUT) I_{RM} Body Diode Reverse Current V_{DS} (DUT) Body Diode Recovery dv/dt V_{SD} V_{DD} Body Diode Forward Voltage Drop Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms





SEMICONDUCTOR

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